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Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^\circ\text{C}$	V_{CE}	1200	V
DC collector current, limited by T_{vjmax} $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_C	50.0 25.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	75.0	A
Turn off safe operating area $V_{CE} \leq 1200\text{V}$, $T_{vj} \leq 150^\circ\text{C}^{1)}$	-	75.0	A
Diode forward current, limited by T_{vjmax} $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_F	50.0 25.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	75.0	A
Gate-emitter voltage Transient Gate-emitter voltage ($t_p \leq 10\mu\text{s}$, $D < 0.010$)	V_{GE}	± 20 ± 25	V
Power dissipation $T_C = 25^\circ\text{C}$ Power dissipation $T_C = 100^\circ\text{C}$	P_{tot}	231.0 92.4	W
Operating junction temperature	T_{vj}	-40...+150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55...+150	$^\circ\text{C}$
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	$^\circ\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

 R_{th} Characteristics

IGBT thermal resistance, junction - case	$R_{th(j-c)}$		-	-	0.54	K/W
Diode thermal resistance, junction - case	$R_{th(j-c)}$		-	-	0.54	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		-	-	40	K/W

¹⁾ $dV/dt < 1\text{KV}/\mu\text{s}$